

b) Amendments to the Claims

Please add new claims 23 and 24 as follows. A detailed listing of all the claims that are or were in the application follows.

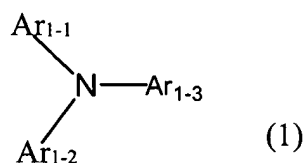
--Claims 1-10 (Cancelled)

11. (Previously Presented) A process cartridge mountable to and detachable from an electrophotographic apparatus having an exposure means comprising a semiconductor laser having an oscillation wavelength of 380 to 500 nm as an exposure light source comprising:

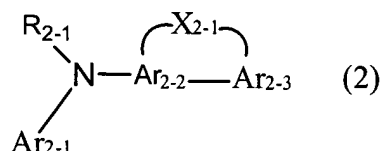
an electrophotographic photosensitive member; and

at least one means selected from a charging means, a developing means and a cleaning means, the electrophotographic photosensitive member being integrately supported by said at least one means;

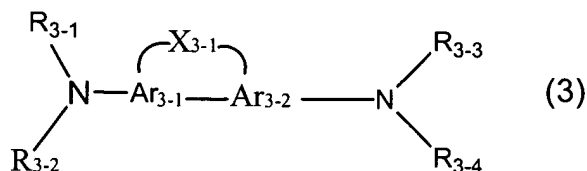
wherein the electrophotographic photosensitive member comprises a conductive substrate, a charge-generating layer formed thereon, said charge generating layer tending to accumulate excess charges upon irradiation with the semiconductor layer exposure light source, and a charge transport layer formed thereon, the charge transport layer having a transmittance of at least 30% for the semiconductor laser light, wherein the charge transport layer contains a charge transfer material represented by the following formulas (1) to (4) and wherein the charge-transfer layer prevents the accumulation of the excess charges:



wherein Ar_{1-1} , Ar_{1-2} and Ar_{1-3} each is a substituted or unsubstituted aromatic group;

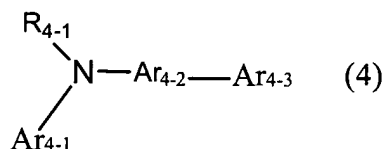


wherein Ar_{2-1} is a substituted or unsubstituted aromatic group, Ar_{2-2} and Ar_{2-3} each is a substituted or unsubstituted aromatic group, R_{2-1} is a substituted or unsubstituted alkyl group, a substituted or unsubstituted aralkyl group, a substituted or unsubstituted vinyl group, or a substituted or unsubstituted aromatic group, X_{2-1} is a divalent organic group, and R_{2-1} and Ar_{2-1} may bond to each other to form a ring;



wherein Ar_{3-1} and Ar_{3-2} each is a substituted or unsubstituted aromatic group, R_{3-1} to R_{3-4} each is a substituted or unsubstituted alkyl group, a substituted or unsubstituted aralkyl group, a substituted or unsubstituted vinyl group, or a substituted or unsubstituted aromatic group wherein at least two of R_{3-1} to R_{3-4} are the substituted or unsubstituted aromatic

groups, X_{3-1} is a divalent organic group, and R_{3-1} and R_{3-2} , or R_{3-3} and R_{3-4} may bond to each other to form a ring; and



wherein Ar_{4-1} and Ar_{4-3} each is a substituted or unsubstituted aromatic group, Ar_{4-2} is a substituted or unsubstituted aromatic group, R_{4-1} is a substituted or unsubstituted alkyl group, a substituted or unsubstituted aralkyl group, a substituted or unsubstituted vinyl group, or a substituted or unsubstituted aromatic group, and Ar_{4-1} and R_{4-1} may bond to each other to form a ring.

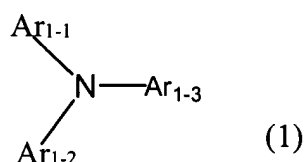
12. (Previously Presented) An electrophotographic apparatus comprising:

- an electrophotographic photosensitive member;
- a charging means;
- an exposure means;
- a developing means; and
- a transfer means;

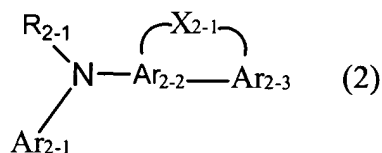
wherein the exposure means comprises a semiconductor laser having an oscillation wavelength of 380 to 500 nm as an exposure light source, and

the electrophotographic photosensitive member comprises a conductive substrate, a charge-generating layer formed thereon, said charge generating layer tending to

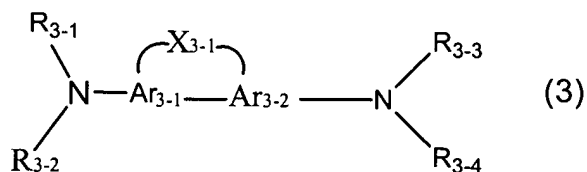
accumulate excess charges upon irradiation with the semiconductor layer exposure light source, and a charge transport layer formed thereon, the charge transport layer having a transmittance of at least 30% for the semiconductor laser light, wherein the charge transport layer contains a charge transfer material represented by the following formulas (1) to (4) and wherein the charge-transfer layer prevents the accumulation of the excess charges:



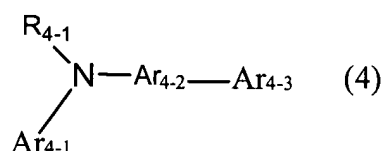
wherein Ar_{1-1} , Ar_{1-2} and Ar_{1-3} each is a substituted or unsubstituted aromatic group;



wherein Ar_{2-1} is a substituted or unsubstituted aromatic group, Ar_{2-2} and Ar_{2-3} each is a substituted or unsubstituted aromatic group, R_{2-1} is a substituted or unsubstituted alkyl group, a substituted or unsubstituted aralkyl group, a substituted or unsubstituted vinyl group, or a substituted or unsubstituted aromatic group, X_{2-1} is a divalent organic group, and R_{2-1} and Ar_{2-1} may bond to each other to form a ring;



wherein Ar_{3-1} and Ar_{3-2} each is a substituted or unsubstituted aromatic group, R_{3-1} to R_{3-4} each is a substituted or unsubstituted alkyl group, a substituted or unsubstituted aralkyl group, a substituted or unsubstituted vinyl group, or a substituted or unsubstituted aromatic group wherein at least two of R_{3-1} to R_{3-4} are the substituted or unsubstituted aromatic groups, X_{3-1} is a divalent organic group, and R_{3-1} and R_{3-2} , or R_{3-3} and R_{3-4} may bond to each other to form a ring; and



wherein Ar_{4-1} and Ar_{4-3} each is a substituted or unsubstituted aromatic group, Ar_{4-2} is a substituted or unsubstituted aromatic group, R_{4-1} is a substituted or unsubstituted alkyl group, a substituted or unsubstituted aralkyl group, a substituted or unsubstituted vinyl group, or a substituted or unsubstituted aromatic group, and Ar_{4-1} and R_{4-1} may bond to each other to form a ring.

13. (Cancelled)

14. (Previously Presented) A process cartridge according to claim 11, wherein the charge transfer material is represented by the formula (1).

15. (Previously Presented) A process cartridge according to claim 11, wherein the charge transfer material is represented by the formula (2).

16. (Previously Presented) A process cartridge according to claim 11, wherein the charge transfer material is represented by the formula (3).

17. (Previously Presented) A process cartridge according to claim 11, wherein the charge transfer material is represented by the formula (4).

18. (Previously Presented) An apparatus according to claim 12, wherein the semiconductor laser light has a wavelength of 400 to 450 nm.

19. (Previously Presented) An apparatus according to claim 12, wherein the charge transfer material is represented by the formula (1).

20. (Previously Presented) An apparatus according to claim 12, wherein the charge transfer material is represented by the formula (2).

21. (Previously Presented) An apparatus according to claim 12, wherein the charge transfer material is represented by the formula (3).

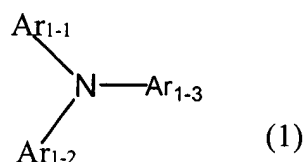
22. (Previously Presented) An apparatus according to claim 12, wherein the charge transfer material is represented by the formula (4).--

23. (New) A process cartridge mountable to and detachable from an electrophotographic apparatus having an exposure means comprising a semiconductor laser having an oscillation wavelength of 380 to 500 nm as an exposure light source comprising:

an electrophotographic photosensitive member; and

at least one means selected from a charging means, a developing means and a cleaning means, the electrophotographic photosensitive member being integrally supported by said at least one means;

wherein the electrophotographic photosensitive member comprises a conductive substrate, a charge-generating layer formed thereon, and a charge transport layer formed thereon, the charge transport layer having a transmittance of at least 30% for the semiconductor laser light, wherein the charge transport layer contains a charge transfer material represented by the following formula (1):



wherein each of Ar_{1-1} , Ar_{1-2} and Ar_{1-3} is a substituted or unsubstituted phenyl group.

24. (New) An electrophotographic apparatus comprising:

an electrophotographic photosensitive member;

a charging means;

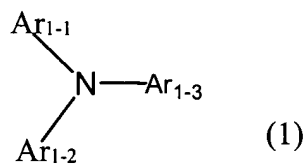
an exposure means;

a developing means; and

a transfer means;

wherein the exposure means comprises a semiconductor laser having an oscillation wavelength of 380 to 500 nm as an exposure light source, and

the electrophotographic photosensitive member comprises a conductive substrate, a charge-generating layer formed thereon, and a charge transport layer formed thereon, the charge transport layer having a transmittance of at least 30% for the semiconductor laser light, wherein the charge transport layer contains a charge transfer material represented by the following formula (1):



wherein each of Ar_{1-1} , Ar_{1-2} and Ar_{1-3} is a substituted or unsubstituted phenyl group.